# EB13C3H1H-13.500M

Vibration



- Nominal Frequency

13 500MHz

Logic Control / Additional Output

Tri-State (High Impedance)

Series RoHS Compliant (Pb-free) Low Current 3.3V 4 Pad 5mm x 7mm Ceramic SMD LVCMOS Oscillator

Frequency Tolerance/Stability

±50ppm over -40°C to +85°C

**Duty Cycle** 

#### 50 ±10(%)

ELECTRICAL SPECIFICATIONS		
Nominal Frequency	13.500MHz	
Frequency Tolerance/Stability	±50ppm over -40°C to +85°C (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Ouput Load Change, First Year Aging at 25°C, Shock, and Vibration)	
Supply Voltage	3.3Vdc ±10%	
Input Current	3mA Maximum	
Output Voltage Logic High (Voh)	90% of Vdd Minimum	
Input Current Logic High (Ioh)	-1.6mA	
Output Voltage Logic Low (Vol)	10% of Vdd Maximum	
Input Current Logic Low (IoI)	+1.6mA	
Rise/Fall Time	6nSec Maximum (Measured at 20% to 80% of waveform)	
Duty Cycle	50 ±10(%) (Measured at 50% of waveform)	
Load Drive Capability	15pF Maximum	

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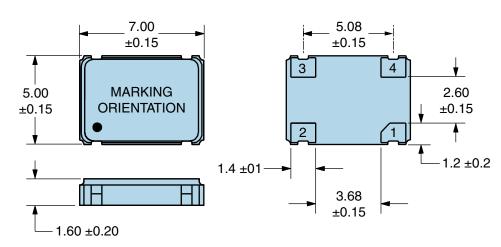
CMOS Output Logic Type Logic Control / Additional Output Tri-State (High Impedance) Tri-State Input Voltage (Vih and Vil) 90% of Vdd Minimum or No Connect to Enable Output, 10% of Vdd Maximum to Disable Output (High Impedance) Standby Current 10µA Maximum (Disabled Output: High Impedance) **One Sigma Clock Period Jitter** 25pSec Maximum Start Up Time 10mSec Maximum Storage Temperature Range -55°C to +125°C

#### **ENVIRONMENTAL & MECHANICAL SPECIFICATIONS Fine Leak Test** MIL-STD-883, Method 1014, Condition A Gross Leak Test MIL-STD-883, Method 1014, Condition C Mechanical Shock MIL-STD-202, Method 213, Condition C **Resistance to Soldering Heat** MIL-STD-202, Method 210 **Resistance to Solvents** MIL-STD-202, Method 215 Solderability MIL-STD-883, Method 2003 **Temperature Cycling** MIL-STD-883, Method 1010

MIL-STD-883, Method 2007, Condition A

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### **MECHANICAL DIMENSIONS (all dimensions in millimeters)**



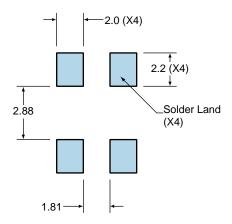
PIN	CONNECTION	
1	Tri-State	
2 3	Ground	
3	Output	
4	Supply Voltage	
LINE MARKING		
LINE	MARKING	
LINE 1	MARKING ECLIPTEK	

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### Suggested Solder Pad Layout

All Dimensions in Millimeters



All Tolerances are ±0.1

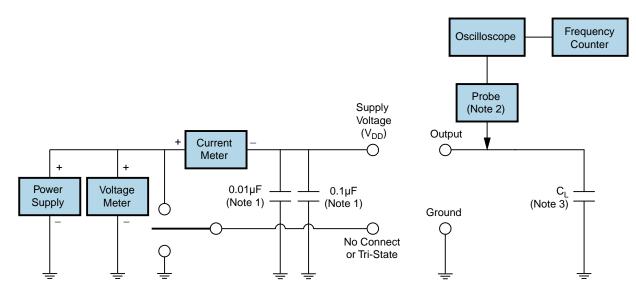
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#### **OUTPUT WAVEFORM & TIMING DIAGRAM**



**Test Circuit for CMOS Output** 



Note 1: An external  $0.1\mu$ F low frequency tantalum bypass capacitor in parallel with a  $0.01\mu$ F high frequency ceramic bypass capacitor close to the package ground and V<sub>DD</sub> pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value  $\dot{C}_L$  includes sum of all probe and fixture capacitance.



## **Recommended Solder Reflow Methods**



### **High Temperature Infrared/Convection**

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$T_s$ MAX to $T_L$ (Ramp-up Rate)	3°C/second Maximum
Preheat	
- Temperature Minimum (T <sub>s</sub> MIN)	150°C
- Temperature Typical (T <sub>s</sub> TYP)	175°C
<ul> <li>Temperature Maximum (T<sub>s</sub> MAX)</li> </ul>	200°C
- Time (t <sub>s</sub> MIN)	60 - 180 Seconds
Ramp-up Rate (T <sub>L</sub> to T <sub>P</sub> )	3°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	217°C
- Time (t∟)	60 - 150 Seconds
Peak Temperature (T <sub>P</sub> )	260°C Maximum for 10 Seconds Maximum
Target Peak Temperature (T <sub>P</sub> Target)	250°C +0/-5°C
Time within 5°C of actual peak (t <sub>p</sub> )	20 - 40 seconds
Ramp-down Rate	6°C/second Maximum
Time 25°C to Peak Temperature (t)	8 minutes Maximum
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.



# **Recommended Solder Reflow Methods**

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### Low Temperature Infrared/Convection 240°C

T <sub>s</sub> MAX to T <sub>L</sub> (Ramp-up Rate)	5°C/second Maximum
Preheat	
- Temperature Minimum (T <sub>s</sub> MIN)	N/A
- Temperature Typical (T <sub>s</sub> TYP)	150°C
<ul> <li>Temperature Maximum (T<sub>s</sub> MAX)</li> </ul>	N/A
- Time (t <sub>s</sub> MIN)	60 - 120 Seconds
Ramp-up Rate (T <sub>L</sub> to T <sub>P</sub> )	5°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	150°C
- Time (t∟)	200 Seconds Maximum
Peak Temperature (T <sub>P</sub> )	240°C Maximum
Target Peak Temperature (T <sub>P</sub> Target)	240°C Maximum 1 Time / 230°C Maximum 2 Times
Time within 5°C of actual peak ( $t_p$ )	10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time
Ramp-down Rate	5°C/second Maximum
Time 25°C to Peak Temperature (t)	N/A
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.

#### Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

### **High Temperature Manual Soldering**

260°C Maximum for 5 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)